

2SC4523

T-35-17



2044

NPN Epitaxial Planar Silicon Transistor

High-Speed Switching Applications

©3142

Features

- Adoption of FBET, MBIT processes
- Large current capacity
- Low collector-to-emitter saturation voltage
- Fast switching speed

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Value	unit
Collector to Base Voltage	V _{CB0}	60	V
Collector to Emitter Voltage	V _{CEO}	45	V
Emitter to Base Voltage	V _{EBO}	5	V
Collector Current	I _C	8	A
Peak Collector Current	i _{cp}	12	A
Collector Dissipation	P _C	1	W
		15	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

T_c = 25°C

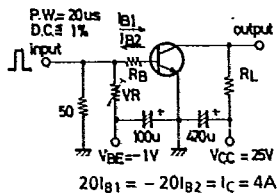
Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Test Conditions	min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} = 45V, I _E = 0			1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = 3V, I _C = 0			1	μA
DC Current Gain	h _{FE} (1)	V _{CE} = 2V, I _C = 500mA	100*		400*	
	h _{FE} (2)	V _{CE} = 2V, I _C = 8A	40			
Gain-Bandwidth Product	f _T	V _{CE} = 2V, I _C = 500mA		250		MHz
Output Capacitance	c _{ob}	V _{CB} = 10V, f = 1MHz		65		pF
C-E Saturation Voltage	V _{CE(sat)}	I _C = 4A, I _B = 200mA	0.25	0.7		V
B-E Saturation Voltage	V _{BE(sat)}	I _C = 4A, I _B = 200mA	0.95	1.3		V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C = 100μA, I _E = 0	60			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	45			V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E = 100μA, I _C = 0	5			V
Turn-ON Time	t _{on}	See specified Test Circuit.		50	100	ns
Storage Time	t _{stg}			150	270	ns
Turn-OFF Time	t _{off}			180	350	ns

* : The 2SC4523 is classified by 500mA h_{FE} as follows :

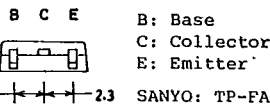
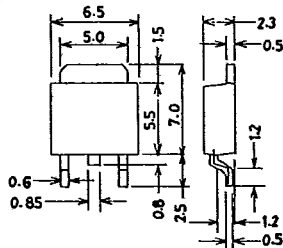
100 R 200	140 S 280	200 T 400
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Switching Time Test Circuit



Case Outline 2044

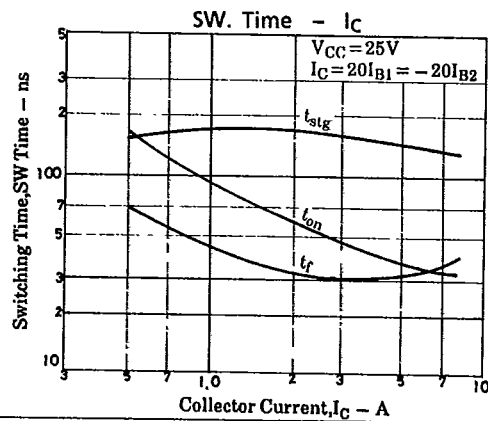
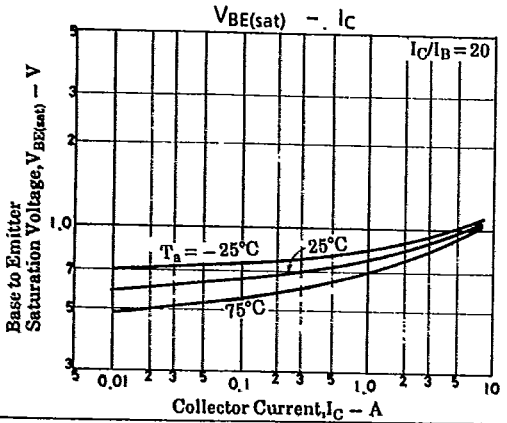
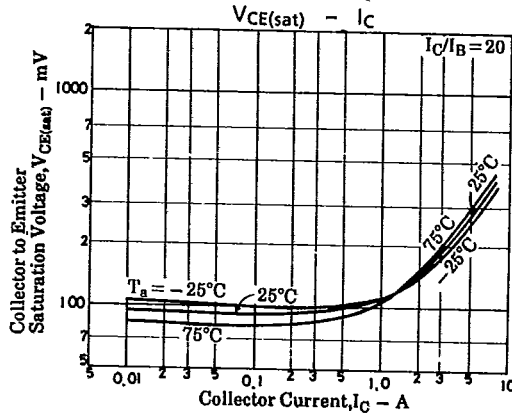
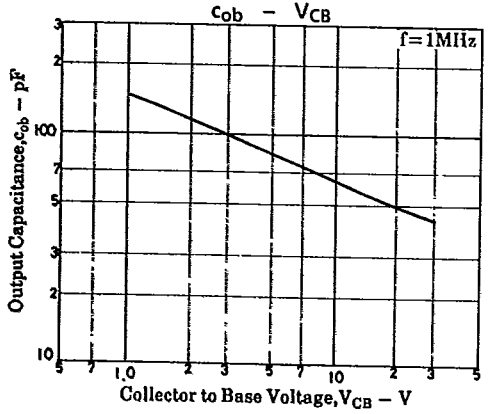
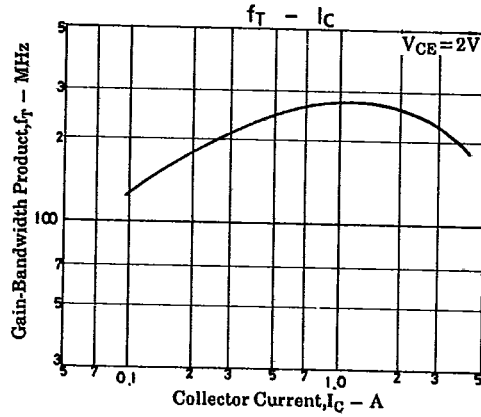
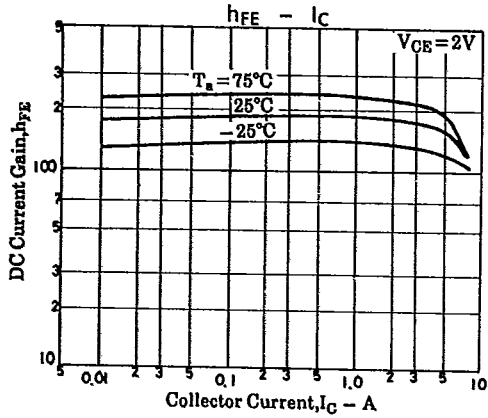
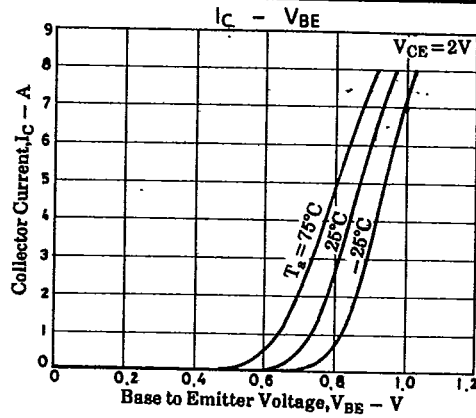
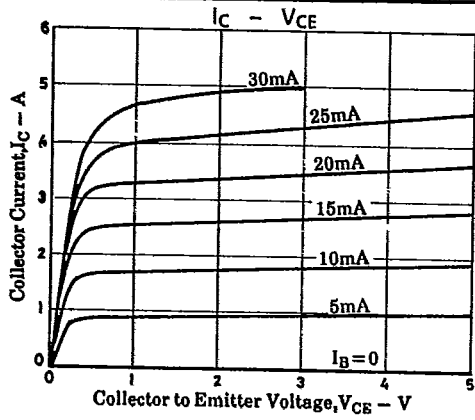
(unit : mm)



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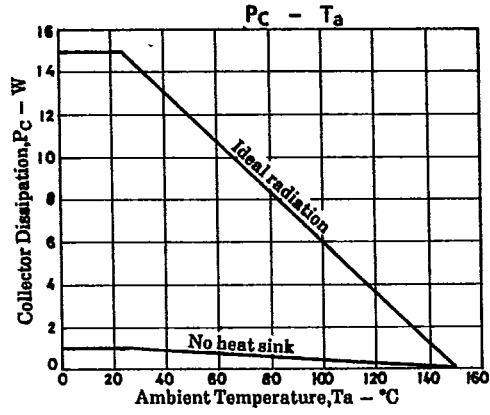
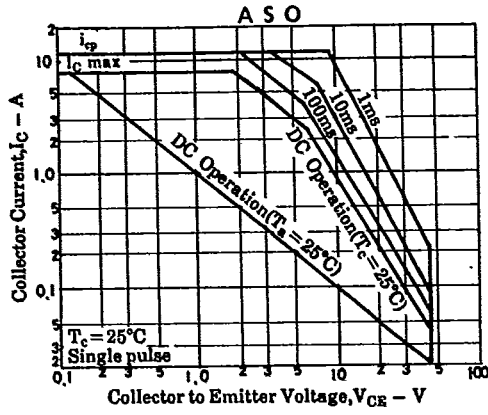
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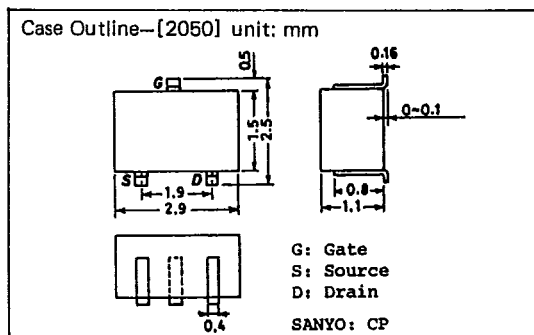
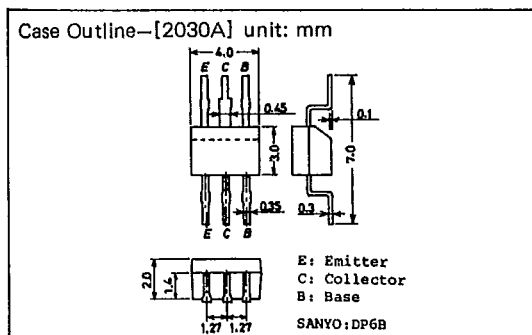
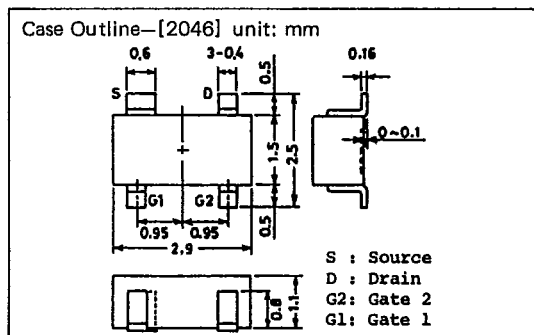
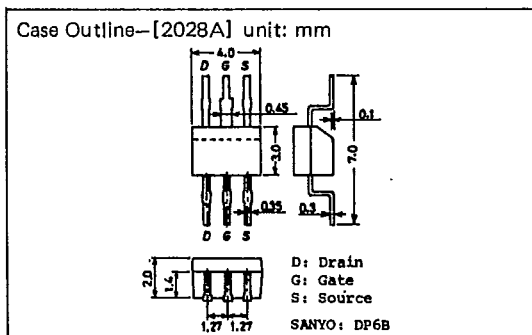
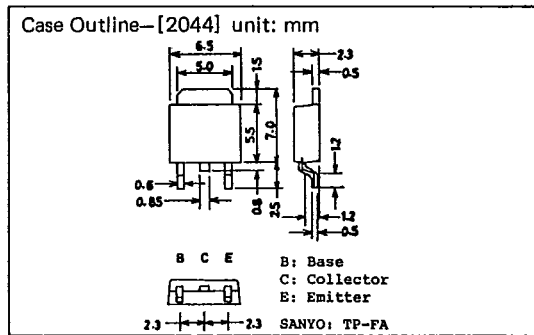
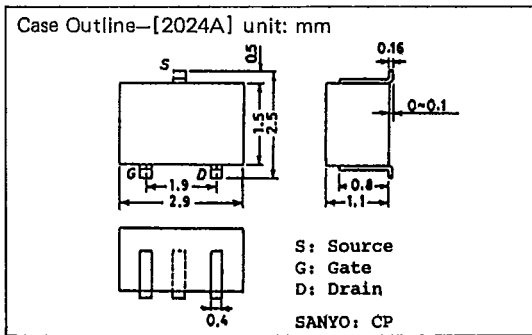
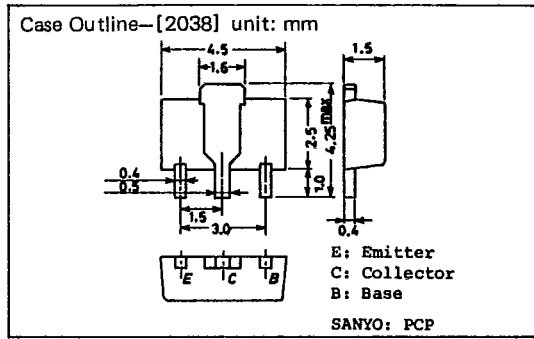
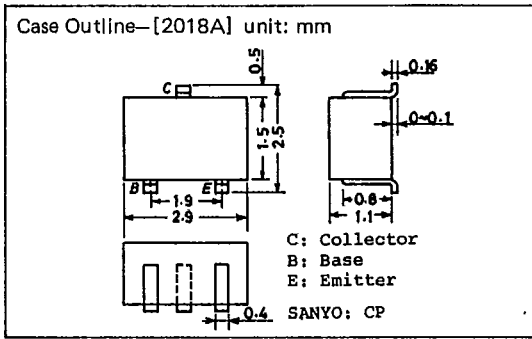
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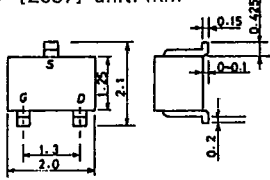
CASE OUTLINES OF SURFACE MOUNT TRANSISTORS

- All of Sanyo surface mount transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.



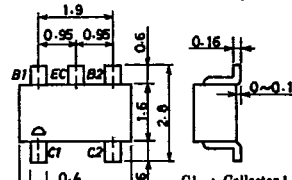
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Case Outline—[2057] unit: mm



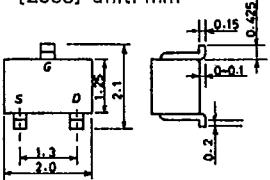
S: Source
G: Gate
D: Drain
SANYO: MCP

Case Outline—[2066] unit: mm



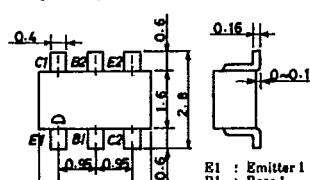
C1 : Collector 1
C2 : Collector 2
B2 : Base 2
EC : Emitter Common
B1 : Base 1
SANYO : CP6

Case Outline—[2058] unit: mm



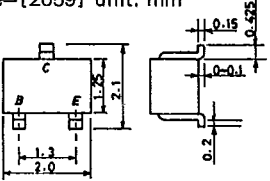
G: Gate
S: Source
D: Drain
SANYO: MCP

Case Outline—[2067] unit: mm



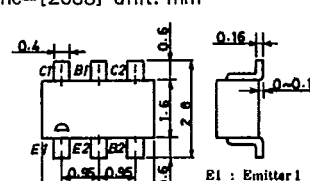
E1 : Emitter 1
B1 : Base 1
C2 : Collector 2
E2 : Emitter 2
B2 : Base 2
C1 : Collector 1
SANYO : CP6

Case Outline—[2059] unit: mm



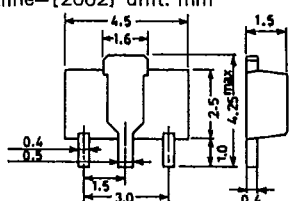
B: Base
C: Collector
E: Emitter
SANYO: MCP

Case Outline—[2068] unit: mm



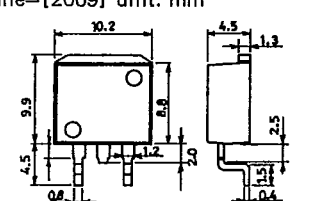
B1 : Emitter 1
E2 : Emitter 2
B2 : Base 2
C2 : Collector 2
B1 : Base 1
C1 : Collector 1
SANYO : CP6

Case Outline—[2062] unit: mm



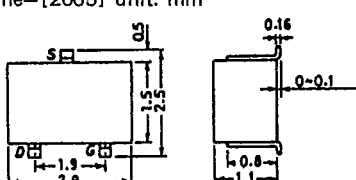
S: Source
D: Drain
G: Gate
SANYO: PCP

Case Outline—[2069] unit: mm



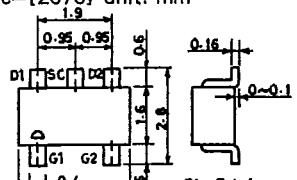
B: Base
C: Collector
E: Emitter
SANYO: SMP

Case Outline—[2065] unit: mm



S: Source
D: Drain
G: Gate
SANYO: CP

Case Outline—[2070] unit: mm



G1 : Gate 1
G2 : Gate 2
D2 : Drain 2
SC : Source Common
D1 : Drain 1
SANYO : CP6

T-9120

